

aSLC

SDHC/SDXC Card 3.0

PHANES-F Series

Document No. : 100-xPSDH-PFITMBAS

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ISO 9001 : 2015 CERTIFIED





Product Features

Flash IC

- TOSHIBA 15nm NAND Flash IC.
- Multi-Level Cell (MLC) management by enhance endurance technology (aSLC)

Compatibility

- SD Memory Card Specifications, Part 1 Physical Layer Specification, version 3.1 Final
- SD Memory Card Specifications, Part 3, Security Specification, Version 3.0 Final

Additional Capabilities

- S.M.A.R.T.¹ (Self-Monitoring, Analysis and Reporting Technology) feature set support.
- Supports SD command Class 6/10
- Supports UHS-1
- Supports SD mode and SPI mode
- Supports CPRM
- Supports Embedded Mode
- Support bad Block Management
- Support both Static and Dynamic Wear Leveling

Mechanical

- 9 exposed contact pins on one side.
- Dimension: 32.0mm x 24.0mm x 2.1mm.
- Weight: 2.5 g / 0.09 oz.

■ Power Operating Voltage 3.3V(+/-) 10%

- Read Mode: 400 mA (max.)
- Write Mode: 400 mA (max.)
- Idle Mode: 1000 uA (max.)

- Performance (Maximum value) *²
 - SDHC card performance

Sequential Read: 99.5 MB/sec. (max.) Sequential Write: 92.7 MB/sec. (max.)

- SDXC card performance Sequential Read: 99.8 MB/sec. (max.) Sequential Write: 93.5 MB/sec. (max.)
- Capacity
 - 4GB, 8GB, 16GB, 32GB, 64GB and 128GB.

Reliability

- ECC: Designed with BCH ECC Algorithm.
- Temperature: (Operating)
 Standard Grade: 0°C ~ +70°C
 Wide Temp. Grade: -40°C ~ +85°C
- Vibration: 80Hz~2000Hz/20G.
- Shock: 0.5ms, 1500 G, 3 axes.
- Erase counts: 20K

Certifications and Declarations

- Certifications: CE & FCC
- Declarations: RoHS & REACH

Remarks:

- 1. Support official S.M.A.R.T. Utility.
- 2. Sequential performance is based on CrystalDiskMark



Order Information

- I. Part Number List
- ♦ APRO aSLC Secure Digital Memory Card PHANES-F Series

| Product Picture | Grade | Wide Temp Grade(-40°C ~ +85°C) |
|-----------------|-------|--------------------------------|
| | 4GB | WPSDH004G-PFITMBAS |
| | 8GB | WPSDH008G-PFITMBAS |
| | 16GB | WPSDH016G-PFITMBAS |
| | 32GB | WPSDH032G-PFITMBAS |
| | 64GB | WPSDX064G-PFITMBAS |
| | 128GB | WPSDX128G-PFITMBAS |

II. Part Number Decoder:

X1 X2 X3 X4 X5 X6 X7 X8 X9–X11 X12 X13 X14 X15 X16 X17 X18

| X1 : Grade | |
|---|-------------------|
| W: Wide Temp Grade- operating ter | np40° C ~ +85 ° C |
| X2 : The material of case | |
| P : Plastic casing | |
| X3 X4 X5 : Product category | |
| SDH : Secure Digital High Capacity | (SDHC) |
| memory card | |
| SDX : Secure Digital eXtended Capa | acity (SDXC) |
| memory card | |
| X6 X7 X8 X9 : Capacity | |
| 004G : 4GB 032G : | 32GB |

| 004G: | 4GB | 032G: | 32GB |
|-------|------|-------|-------|
| 008G: | 8GB | 064G: | 64GB |
| 016G: | 16GB | 128G: | 128GB |

X11 : Controller

P: PHANES Series

X12 : Controller version

A, B, C.....

X13 : Controller Grade

X14 : Flash IC T : Toshiba NAND Flash IC

X15 : Flash IC grade / Type M : MLC -NAND Flash IC

X16 : Flash IC B : Toshiba 15nm MLC

X17 X18 : Flash IC grade / Type

 $\ensuremath{\textbf{AS}}$: aSLC Technology extends MLC product's lifespan



Revision History

| Revision | Description | Date |
|----------|------------------------------|------------|
| 1.0 | Initial release | 2016/06/30 |
| 1.1 | Add. 64GB & 128GB Capacities | 2018/04/10 |
| 2.0 | Updated Document form | 2019/06/17 |

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1. Introduction

APRO aSLC Secure Digital Memory Card PHANES-F Series, is specifically designed to meet the security, performance and environmental requirements of some significant applications such like networking, telecommunications and data-communications, mobile & embedded computing, medical instruments and industrial computing applications.

The main used Flash memory is aSLC-NAND Type Flash memory chips are 4GB, 8GB, 16GB, 32GB, 64GB and 128GB. APRO aSLC Micro SD Cards include a copyright protection that complies with the security of the SDMI standard, and the physical form-factor, pin assignment.

1.1. Scope

This document describes the key features and specifications of APRO aSLC Secure Digital Memory Cards.

1.2. Flash Management Technology – Static & Dynamic Wear Leveling

NAND flash devices can only undergo a limited number of program/erase cycles, and in most cases, the flash media are not used evenly. If some areas get updated more frequently than others, the lifetime of the device would be reduced significantly. Thus, Wear Leveling is applied to extend the lifespan of NAND Flash by evenly distributing write and erase cycles across the media.

APRO aSLC Secure Digital Memory Card PHANES-F Series provides advanced Wear Leveling algorithm, which can efficiently spread out the flash usage through the whole flash media area. Moreover, by implementing both dynamic and static Wear Leveling algorithms, the life expectancy of the NAND flash is greatly improved.

1.3. Bad Block Management

Early Bad Block

The fault block generated during the manufacturing process of NAND Flash is called Early Bad Block.

Later Bad Block

In the process of use, as the number of operations of writing and erasing increases, a fault block is gradually generated, which is called a Latter Bad Block.

Bad block management is a management mechanism for a bad block to be detected by the control IC and mark bad blocks in the NAND Flash and improve the reliability of data access. The bad block management mechanism of the control IC will establish a **Bad Block Table** when the NAND Flash is started for the first time, and will also record the errors found in the process of use in the bad block table, and data is ported to new valid blocks to avoid data loss.

In order to detect the initial bad blocks to handle run time bad blocks, APRO aSLC Secure Digital Memory Card PHANES-F Series provides the **Bad Block Management** scheme. It remaps a bad block to one of the reserved blocks so that the data contained in one bad block is not lost and new data writes on a bad block is avoided.

1.4. Embedded Mode

Embedded mode is a function specially designed for operating systems that do not utilize FAT. Often under non Windows OS, for example Linux or customized host, wear leveling mechanism of APRO aSLC MicroSD cards will be affected or even disabled in some cases. With embedded mode activated, aSLC MicroSD cards ensure that under any circumstances, wear leveling mechanism can operate normally to keep the usage of blocks even throughout the MicroSD card's life cycle. This is especially a great add-on for security cameras or drive recorders.

1.5. aSLC Technology

The aSLC can be considered as an extended version of the MLC. While MLC contains both fast and slow pages, aSLC only utilizes fast pages for programming. The concept of aSLC is demonstrated in the Figure 2 below. The first and second bits of a memory cell represent a fast and slow page respectively, as shown in the left table. Since only fast pages are programmed when applying aSLC, the bits highlighted in red are used, as shown in the right table. As a result, aSLC provides better performance and endurance than MLC does. Moreover, the aSLC performs similarly to the SLC, yet more cost effective

| MLC | Flash | | aSLC | : Flash |
|----------------------------|----------------------------|---------------|----------------------------|----------------------------|
| 1 st bit (fast) | 2 nd bit (slow) | | 1 st bit (fast) | 2 nd bit (slow) |
| 1 | 1 | | 1 | 1 |
| 1 | 0 | \rightarrow | 1 | 0 |
| 0 | 1 | | 0 | 1 |
| 0 | 0 | | 0 | 0 |

Figure 1: The concept of APRO aSLC technology

2. Product Specifications

For all the following specifications, values are defined at ambient temperature and nominal supply voltage unless otherwise stated.

2.1. System Environmental Specifications

| APRO aSLC Secure Digital Memory Card | | Wide temp Grade | |
|--------------------------------------|----------------------------|--------------------------|--|
| PHANES-F Series | | WPSDHXXXG-PFITMBAS | |
| Tomo orativo | Operating: | -40°C ~ +85°C | |
| Temperature | Non-operating: | -50°C ~ +95°C | |
| Humidity | Operating & Non-operating: | 10% ~ 95% non-condensing | |
| Vibration | Operating & Non-operating: | 80Hz~2000Hz/20G. | |
| Shock | Operating & Non-operating: | 0.5ms, 1500 G, 3 axes | |

2.2. System Power Requirements

Table 2: Power Requirement

| APRO aSLC Secure Digital Memory Card PHANES-F Series | | Wide temp Grade | | |
|--|----------------------|--------------------|--|--|
| APRO astc secure Digital Memory | Card PHANES-F Series | WPSDHXXXG-PFITMBAS | | |
| DC Input Voltage (VCC) | | 3.3V±10% | | |
| | Reading Mode : | 400 mA (max.) | | |
| Maximum average value | Writing Mode : | 400 mA (max.) | | |
| | I dle Mode : | 1000 uA (max.) | | |

2.3. System Performance

Table 3: System Performances

| Data Transfer Mode supporting | | SDA Specification Ver 3.0 (UHS-1, Grade 3) | | | | | |
|-------------------------------|-------------------------|--|------|-----------------|------|-----------------|-------|
| Capacity level | | SDHC | | | SDXC | | |
| Speed level | | UHS-1 (Grade-1) | | UHS-1 (Grade-3) | | UHS-1 (Grade-3) | |
| Maximum Performance | Capacity | 4GB | 8GB | 16GB | 32GB | 64GB | 128GB |
| | Sequential Read (MB/s) | 97.5 | 99.5 | 99.5 | 99.5 | 99.8 | 99.8 |
| | Sequential Write (MB/s) | 80.2 | 92.4 | 92.7 | 92.6 | 93.5 | 93.5 |

Note:

> All values quoted are typically at $25\,^\circ\!C$ and nominal supply voltage.

> The performance is obtained from TestMetrix Test (@500MB).

2.4. System Reliability

Table 4: System Reliability

| Wear-leveling Algorithms | Static and Dynamic wear-leveling algorithms |
|-------------------------------|--|
| Bad Blocks Management | Supportive |
| ECC Technology | BCH ECC |
| Endurance | NAND MLC Flash w/aSLC Technology : 20K Erase counts |
| Durability | 10,000 inserting cycles |
| Bending | >10N |
| Torque | 0.1N +/- 2.5 deg. |
| Drop Test | 1.5M free fall |
| Salt Spray | Concentration: 3% NaCl/35℃ |
| Waterproof | 1000mm submerge for 30 minutes, IPx7 compliance |
| Electrostatic Discharge (ESD) | Contact: +/- 4KV each item 5 times |
| Electrostatic Discharge (ESD) | Air: +/- 8KV 10 times |
| | 0.1 Gy of medium energy radiation (70 keV to 140keV, cumulative does per |
| X-Ray Exposure Test | year) to both sides of the card. |

Note:

> The endurance of SSD could be estimated based on user behavior, NAND endurance cycles, and write amplification factor.

It is not guaranteed by flash vendor.

2.5. Physical Specifications

Refer to Table 5 and see Figure 1 for APRO aSLC Secure Digital Memory Card PHANES-F Series physical specifications and dimensions.

| Table 5: Physical Specifications of APRO aSLC Secure Digital Memory Card PHANES- | - Series |
|--|----------|
| | |

| Length: | 32.00 mm | | |
|------------|-----------------|--|--|
| Width: | 24.00 mm | | |
| Thickness: | 2.10 mm | | |
| Weight: | 2.5 g / 0.09 oz | | |

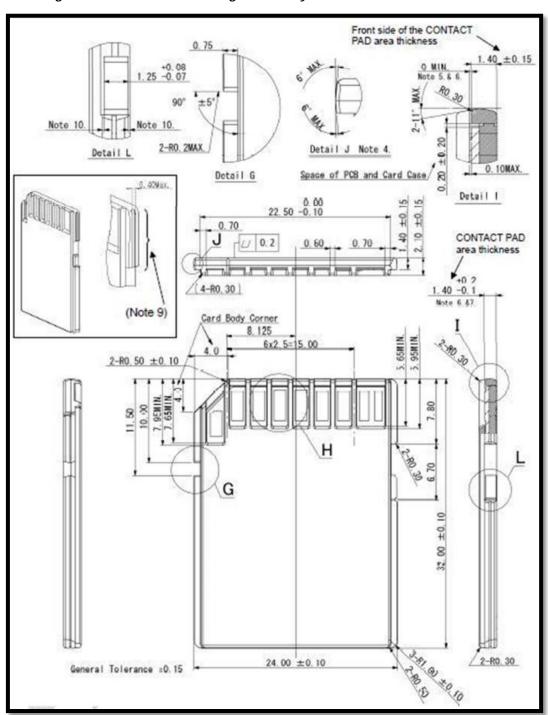


Figure 2: APRO aSLC Secure Digital Memory Card PHANES-F Series Dimension

3. Interface Description

3.1. Secure Digital Memory Card interface

APRO aSLC Secure Digital Memory Card PHANES-F Series has 9 exposed contacts on one side.

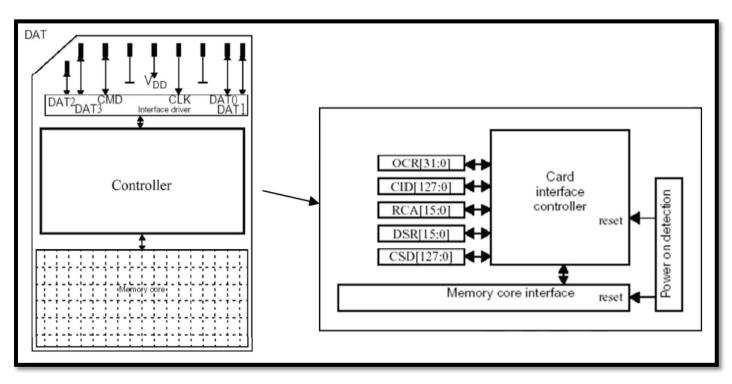


Figure 3: 9 Pins Connector

3.2. Pin Assignments

APRO

| Pin Number | |) Mode | SPI Mode | | | |
|------------|------------------------|-------------------------|--------------------------------|-----------|----------------|-----------------------|
| | Pin Name | Type ¹ | Description | Pin Name | Туре | Description |
| Pin 1 | CD / DAT3 ² | I/O/PP ³ | Card Detect / Data Line [bit3] | CS | I ³ | Chip Select |
| Pin 2 | CMD | CMD PP Command / Re | | DI | I | Data in |
| Pin 3 | V _{SS1} | S Supply voltage ground | | V_{SS} | S | Supply voltage ground |
| Pin 4 | V _{DD} | S | Supply voltage | V_{DD} | S | Supply voltage |
| Pin 5 | CLK | I | Clock | SCLK | I | Clock |
| Pin 6 | V _{SS2} | S | Supply voltage ground | V_{SS2} | S | Supply voltage ground |
| Pin 7 | DATO | I/O/PP | Data Line [bit0] | DO | O/PP | Data Out |
| Pin 8 | DAT1 | I/O/PP | Data Line [bit1] | RSV | | |
| Pin 9 | DAT2 | I/O/PP | Data Line [bit2] | RSV | | |

There are total of 8 pins in the Micro SD Connector. The pin assignments are listed in below table 6.

| Table | 6 | _ | Pin | Assignments |
|-------|---|---|-----|-------------|
| Tubic | ~ | | | Assignments |

S: power supply, I:input; O:output using push-pull drivers; PP:I/O using push-pull drivers.

The extended DAT lines (DAT1-DAT3) are input on power up. They start to operate as DAT lines after SET_BUS_WIDTH command. The Host shall keep its own DAT1-DAT3 lines in input mode, as well, while they are not used. It is defined so, in order to keep compatibility to Multi-Media Cards.

At power up this line has a 50KOhm pull up enabled in the card. This resistor serves two functions Card detection and Mode Selection. For Mode Selection, the host can drive the line high or let it be pulled high to select SD mode. If the host wants to select SPI mode it should drive the line low. For Card detection, the host detects that the line is pulled high. This pull-up should be disconnected by the user during regular data transfer period, withSET_CLR_CARD_DETECT(ACMD42) command.

Appendix A: Limited Warranty

APRO warrants your aSLC Secure Digital Memory Card PHANES-F Series against defects in material and workmanship for the life of the drive. The warranty is void in the case of misuse, accident, alteration, improper installation, misapplication or the result of unauthorized service or repair. The implied warranties of merchantability and fitness for a particular purpose, and all other warranties, expressed or implied, except as set forth in this warranty, shall not apply to the products delivered. In no event shall APRO be liable for any lost profits, lost savings or other incidental or consequential damages arising out of the use of, or inability to use, this product.

BEFORE RETURNING PRODUCT, A RETURN MATERIAL AUTHORIZATION (RMA) MUST BE OBTAINED FROM APRO.

Product shall be returned to APRO with shipping prepaid. If the product fails to conform based on customers' purchasing orders, APRO will reimburse customers for the transportation charges incurred.

WARRANTY PERIOD:

aSLC (Standard grade / Wide temp. grade) 2 years / Within 20K Erasing Counts

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